

Understanding the Limitations and Improving the Relevance of SPICE Simulations in Security Evaluations

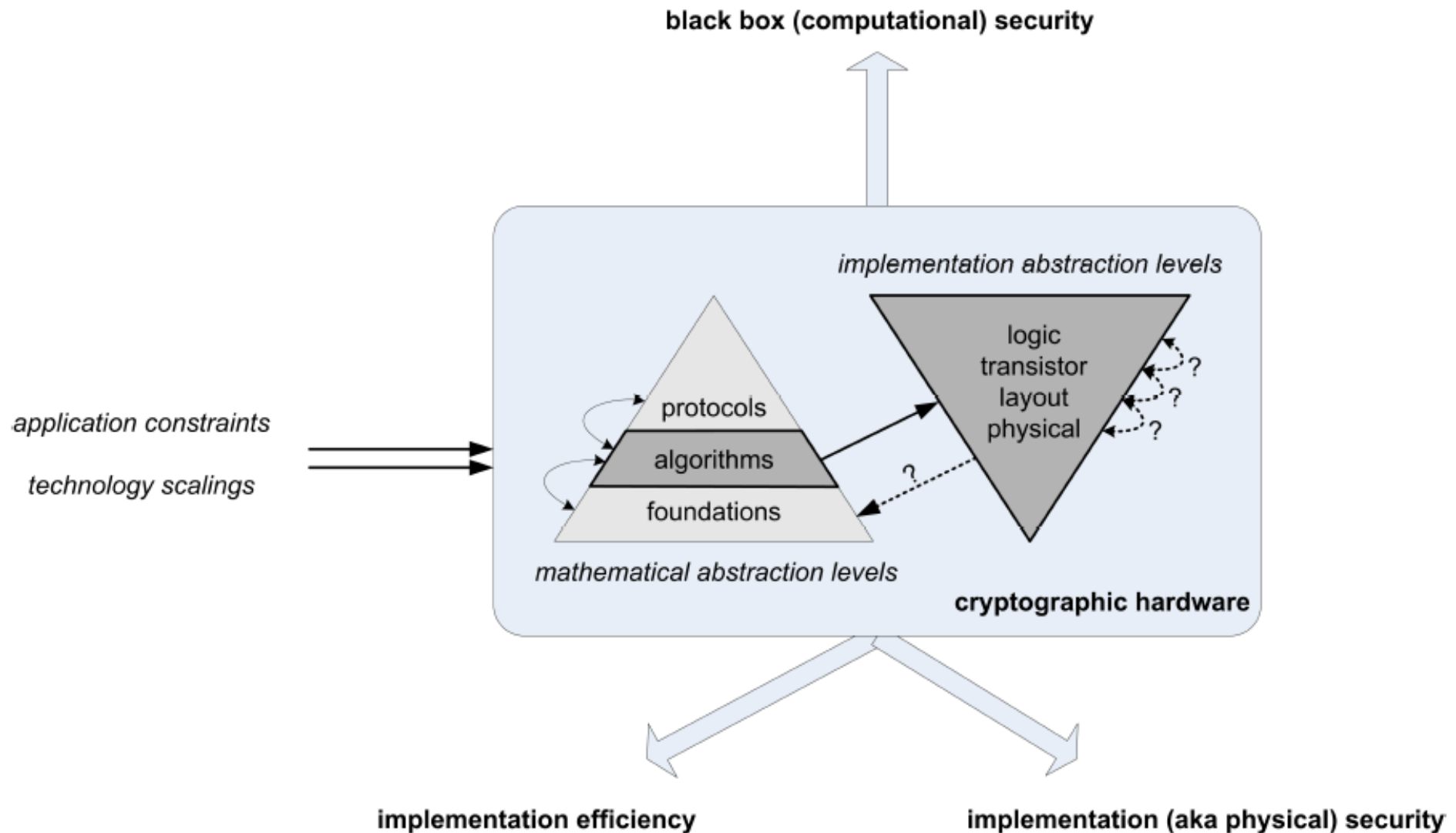
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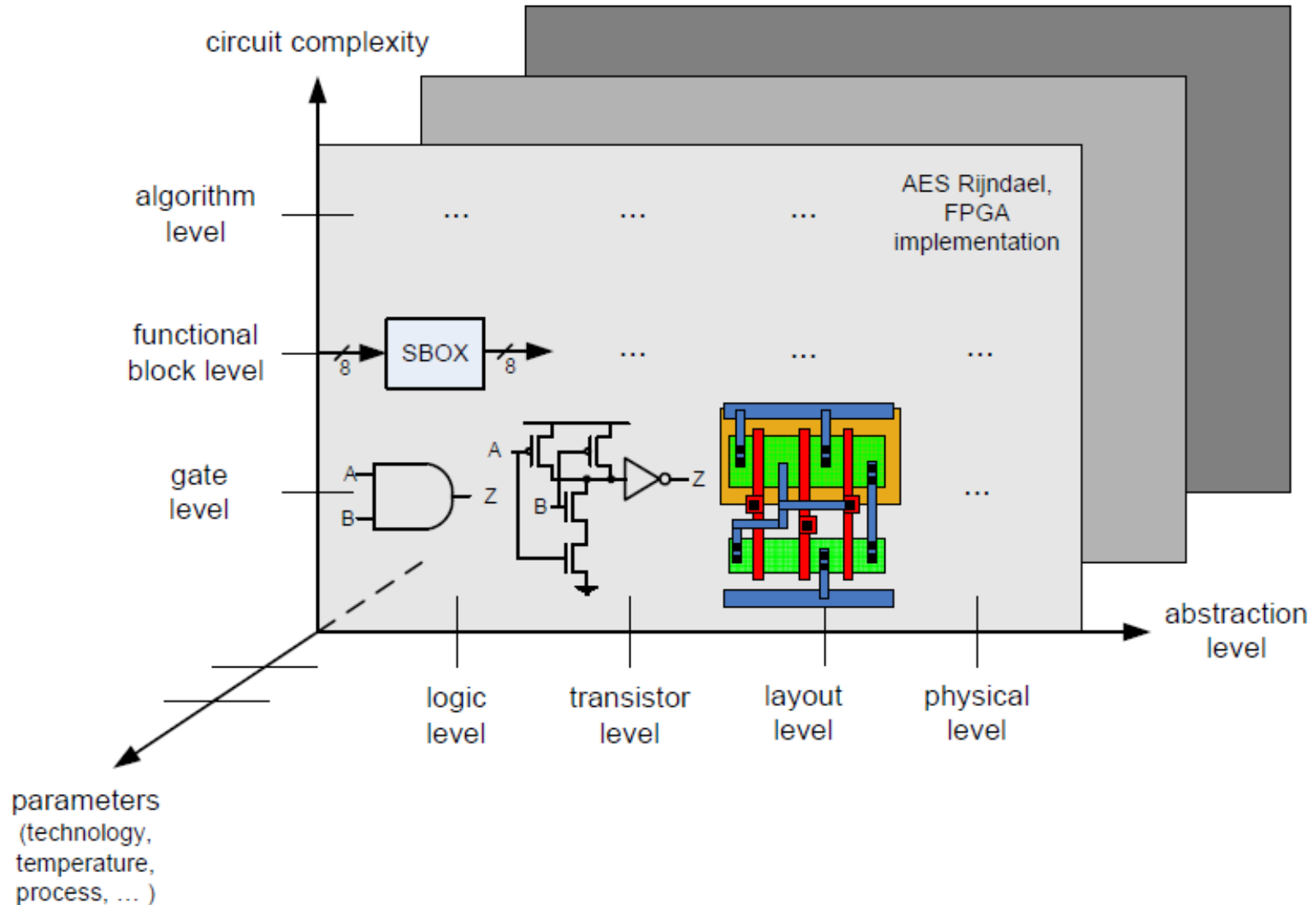
PROOFS 2013
Santa Barbara, USA



The cryptographic HW design space



Multidimensional problem



Problem statement

- SCA countermeasures are expensive
- Confident evaluations require silicon
- But testing all ideas up to silicon is not realistic

⇒ We need to exploit the simulation paradigm

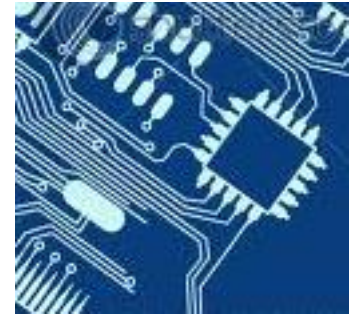
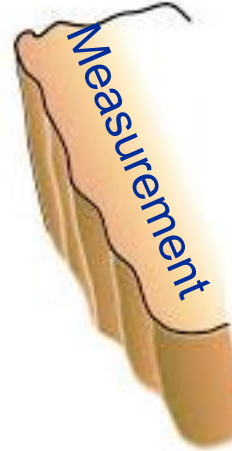
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- As for any hardware optimization criteria!
- Being aware of its limitations
(i.e. knowing what can and cannot be learned)
- Main goal: avoid false negatives

Current situation



- Simulations and measurements differ
 - Quantitatively (amount of information leakage)
 - Qualitatively (nature of the information leakage)

Example

- DDSLL (dynamic and differential) S-box
- 65-nanometer technology
- Evaluated with the perceived information

$$\hat{M}(K; L) = H[K] - \sum_{k \in \mathcal{X}} \Pr[k] \sum_{l \in \mathcal{L}} \Pr_{\text{chip}}[l|k] \log_2 \hat{\Pr}_{\text{model}}[k|l]$$

\hat{P}_l

= estimator of the MI, biased by the adversary's model

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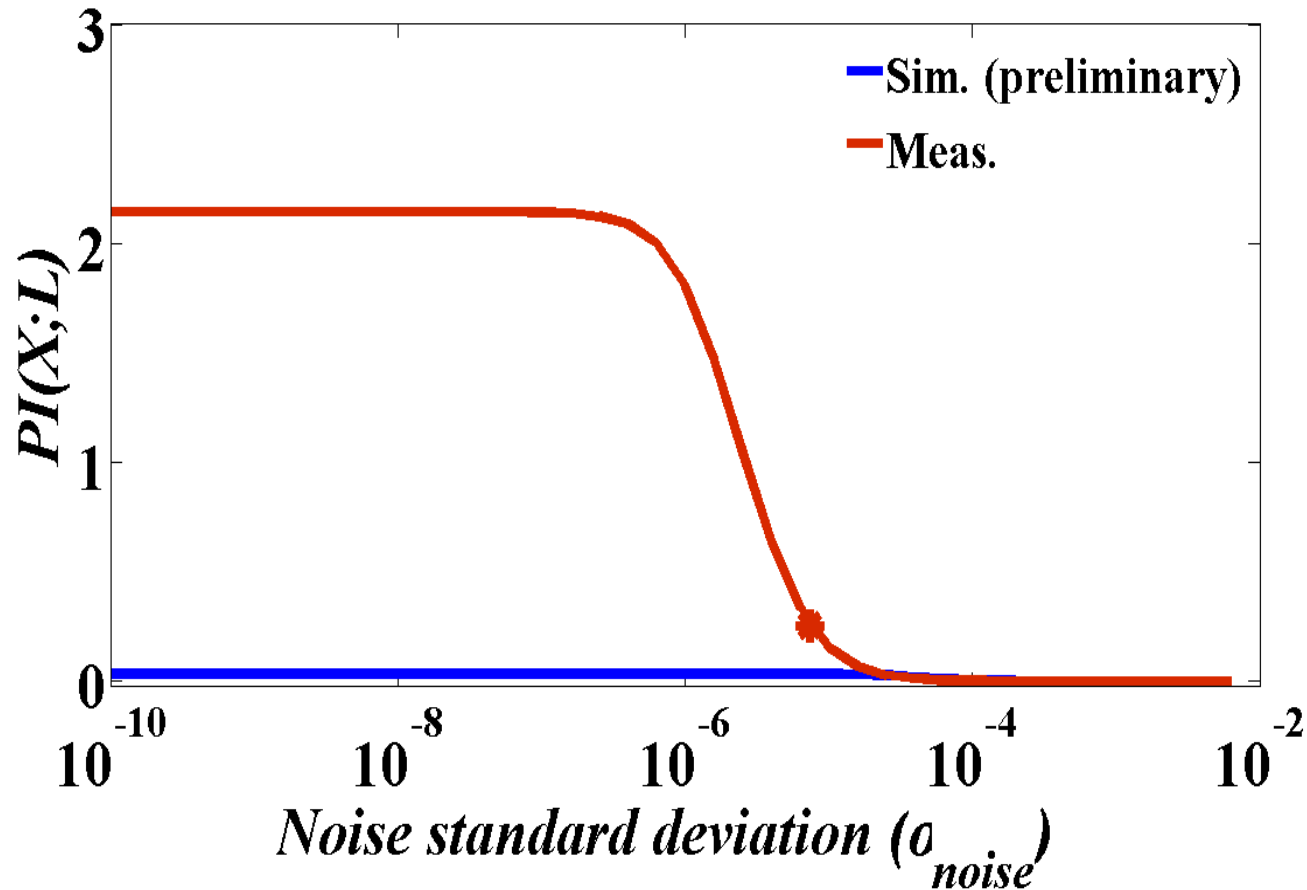
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- Can be estimated, e.g. from
 - Gaussian templates
 - Linear regression with linear basis
 - (allows measuring the measurements “linearity”)

CHES 2011 results

- Regression-based information theoretic evaluation



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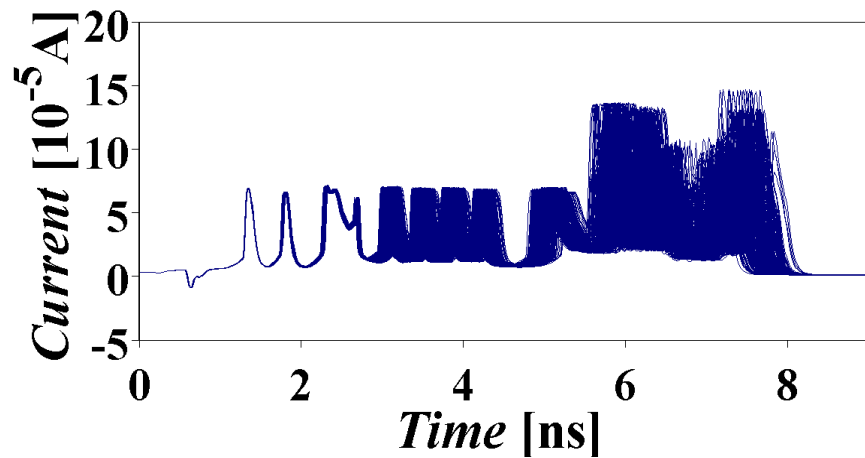
- The linearity of the measurements is an important criteria for the application of non-profiled DPA
- [VS11,WOS12]: generic attacks are only possible in the context of “sufficiently linear” leakages
 - One hope for dual-rail logic styles is to provide highly non-linear leakages (to avoid these attacks)
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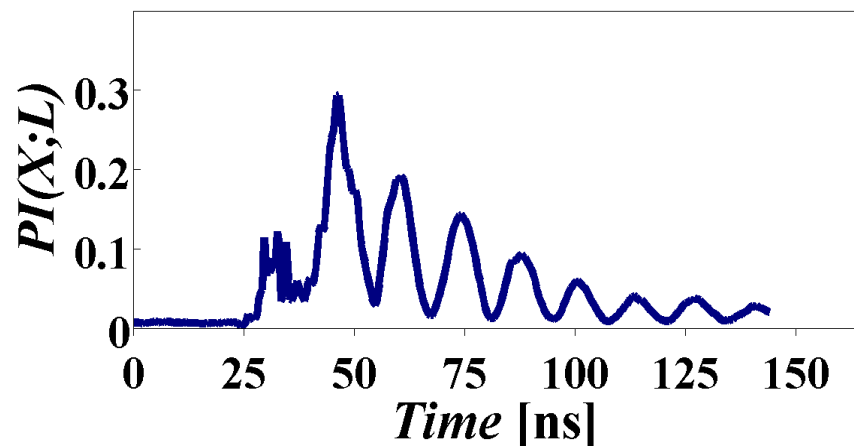
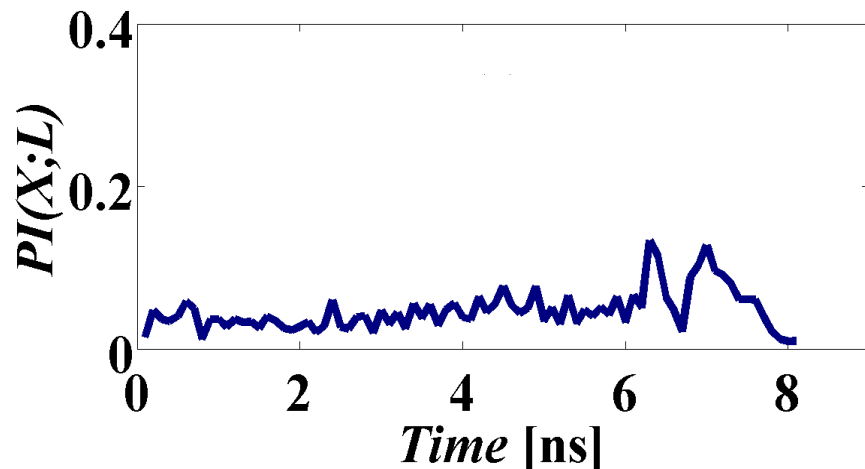
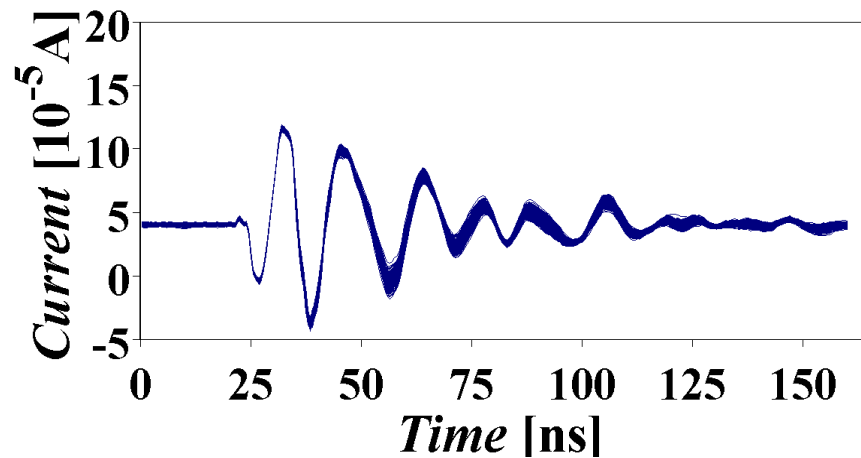
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 - One hope for dual-rail logic styles is to provide highly non-linear leakages (to avoid these attacks)
⇒ Simulations are misleading with this respect
- Our goal: *understanding why, improving if possible!*

Step 1: looking at the traces

Simulation

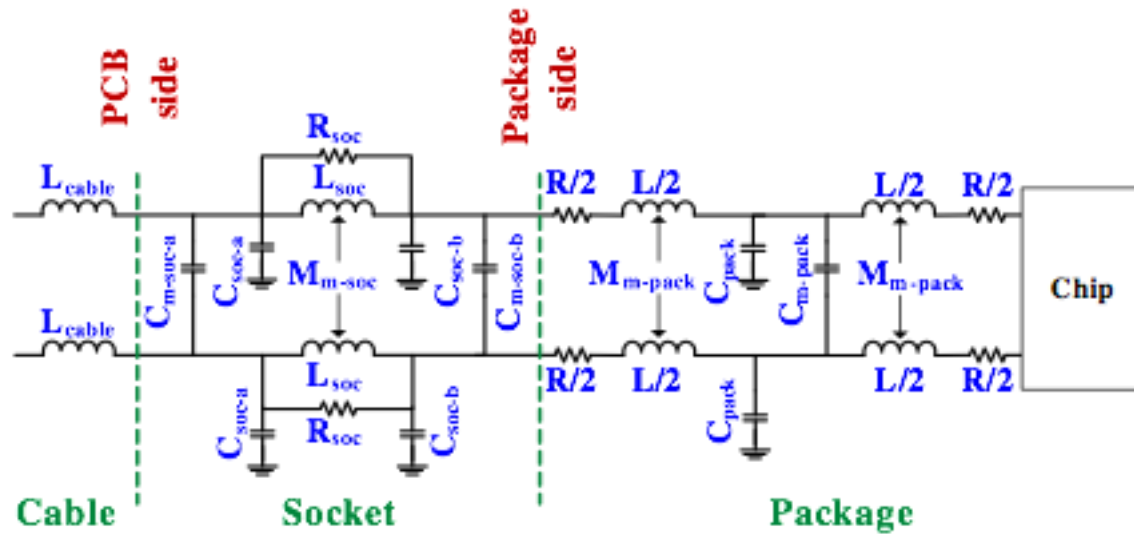


Measurement (real noise $6e^{-6}$)

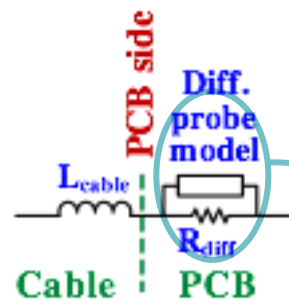


Step 2: trying to model

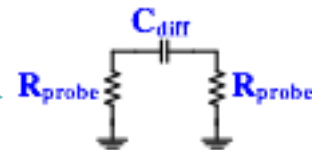
- Equivalent circuit model (generic)



(a)



(b)



(c)

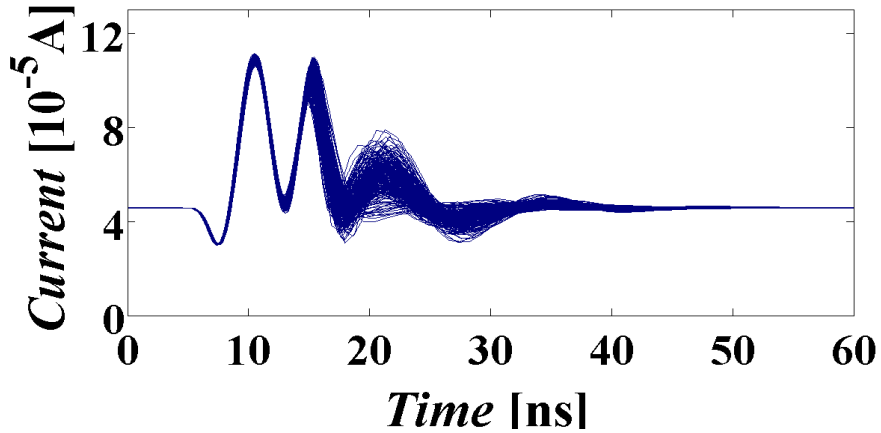
Step 3: instantiating the model

Element	Symbol	Description	Value
Cable	L_{cable}	Supply inductance	688 nH
		In/out inductance	300 nH
		GND inductance	200 nH
Socket	L_{soc}	Lead inductance	1.35 nH
	R_{soc}	Parallel lead res.	600 Ω
	$C_{\text{soc-a}}$	Cap. to GND (PCB side)	0.3 pF
	$C_{\text{soc-b}}$	Cap. to GND (pack. side)	0.45 pF
	$L_{\text{m-soc}}$	Mutual inductance	0.3 nH
	$C_{\text{m-soc-a}}$	Mutual cap. (PCB side)	0.09 pF
	$C_{\text{m-soc-b}}$	Mutual cap. (pack. side)	0.09 pF
Package	L	Inductance	1.2 nH
	R	Series resistance	0.28 Ω
	C_{pack}	Cap. To GND	0.1 pF
	$L_{\text{m-pack}}$	Mutual inductance	1.3 nH
	$C_{\text{m-pack}}$	Mutual cap.	0.2 pF
Diff. Probe	C_{diff}	Capacitance	0.7 pF
	R_{probe}	Resistance	25 k Ω
	R_{diff}	Res. in S-box VDD path	1 k Ω

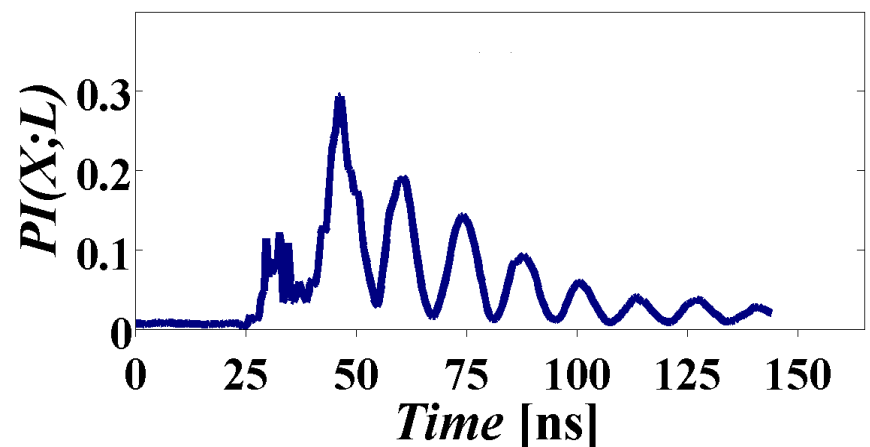
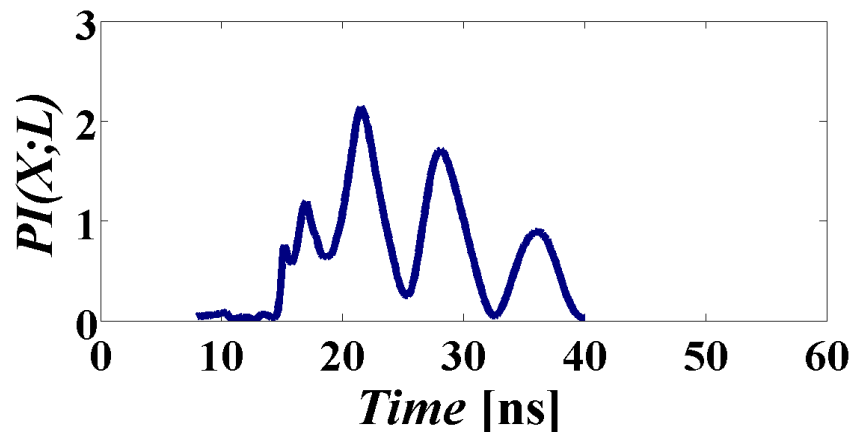
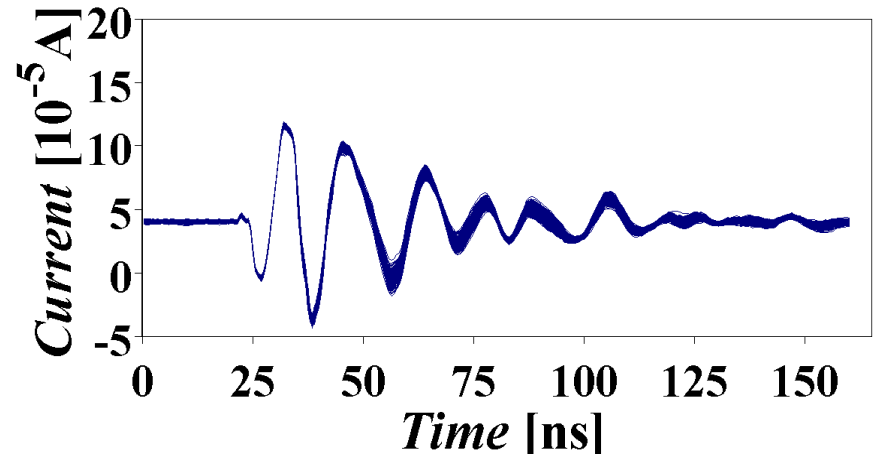
- The more precise the better (specific)
 - (but we sometimes had only approximations)

Example: looking at the traces again

Simulation with circuit model



Measurement (real noise $6e^{-6}$)



Step 4: how precise must the model be?

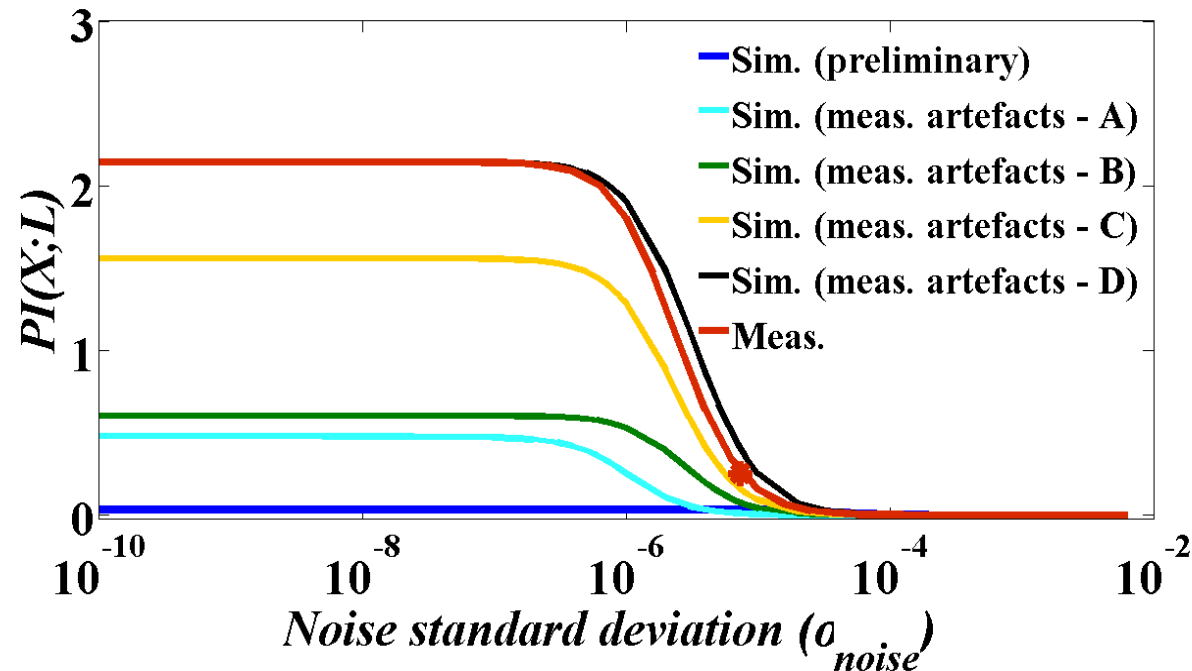
- Our strategy: use increasingly complex ones

Model	Description
A	1 k Ω + diff. probe
B	1 k Ω + diff. probe + pack. and socket
C	1 k Ω + diff. probe + pack. and socket + V _{DD} cable
D	1 k Ω + diff. probe + pack. and socket + V _{DD} cable + GND cable

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- Modeling circuit / measurement specificities is crucial
 - It increases the relevance of simulations
 - ⇒ Reduces the risk of false negatives
 - Even with imprecise instantiation of the model!
 - ⇒ Reasonably generic approach

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 - (already for a simple S-box circuit)
- Modeling circuit / measurement specificities is crucial
 - It increases the relevance of simulations
 - ⇒ Reduces the risk of false negatives
 - Even with imprecise instantiation of the model!
 - ⇒ Reasonably generic approach
- Designing circuits with highly non-linear leakages seems challenging (filters linearize them)

THANKS

<http://perso.uclouvain.be/fstandae/>